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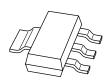
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Kind regards,

Team Nexperia



PBSS9110Z 100 V, 1 A PNP low V_{CEsat} (BISS) transistor Rev. 03 — 11 December 2009

Product data sheet

Product profile 1.

1.1 General description

PNP low V_{CEsat} Breakthrough In Small Signal (BISS) transistor in a SOT223 (SC-73) small Surface-Mounted Device (SMD) plastic package.

NPN complement: PBSS8110Z.

1.2 Features

- Low collector-emitter saturation voltage V_{CEsat}
- High collector current capability I_C and I_{CM}
- High collector current gain (h_{FE}) at high I_C
- High efficiency due to less heat generation
- Smaller required Printed-Circuit Board (PCB) area than for conventional transistors

1.3 Applications

- High-voltage DC-to-DC conversion
- High-voltage MOSFET gate driving
- High-voltage motor control
- High-voltage power switches (e.g. motors, fans)
- Automotive applications

1.4 Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
V_{CEO}	collector-emitter voltage	open base	-	-	-100	V
I _C	collector current		-	-	-1	А
I _{CM}	peak collector current	single pulse; $t_p \leq 1 \text{ ms}$	-	-	-3	A
R _{CEsat}	collector-emitter saturation resistance	I _C = -1 A; I _B = -100 mA	<u>[1]</u> _	170	320	mΩ

[1] Pulse test: $t_p \le 300 \ \mu s$; $\delta \le 0.02$.



100 V, 1 A PNP low V_{CEsat} (BISS) transistor

2. Pinning information

Pin	Description	Simplified outline	Symbol
1	base		
2	collector		2, 4
3	emitter		1
4	collector		3
			sym028

3. Ordering information

Table 3. Ordering information					
Type number	Package				
	Name	Description	Version		
PBSS9110Z	SC-73	plastic surface-mounted package with increased heat sink; 4 leads	SOT223		

4. Marking

Table 4. Marking codes	
Type number	Marking code
PBSS9110Z	PB9110

5. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit
V _{CBO}	collector-base voltage	open emitter	-	-120	V
V _{CEO}	collector-emitter voltage	open base	-	-100	V
V _{EBO}	emitter-base voltage	open collector	-	-5	V
I _C	collector current		-	-1	А
I _{CM}	peak collector current	single pulse; $t_p \leq 1 \text{ ms}$	-	-3	А
I _B	base current		-	-0.3	А
P _{tot}	total power dissipation	$T_{amb} \leq 25 ~^{\circ}C$	<u>[1]</u> -	0.65	W
			[2] _	1	W
			[3]	1.4	W

100 V, 1 A PNP low V_{CEsat} (BISS) transistor

Table 5. Limiting values ...continued

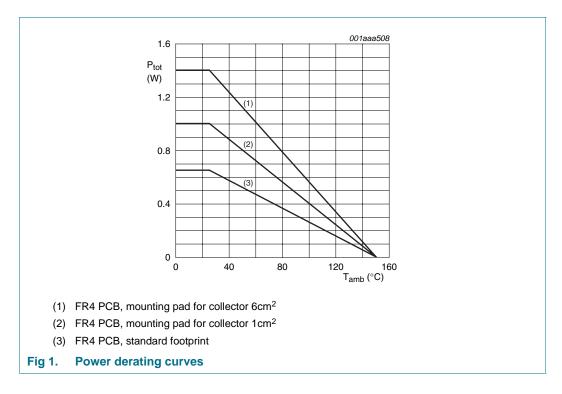
In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit
Tj	junction temperature		-	150	°C
T _{amb}	ambient temperature		-65	+150	°C
T _{stg}	storage temperature		-65	+150	°C

[1] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.

[2] Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for collector 1cm².

[3] Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for collector 6cm².



6. Thermal characteristics

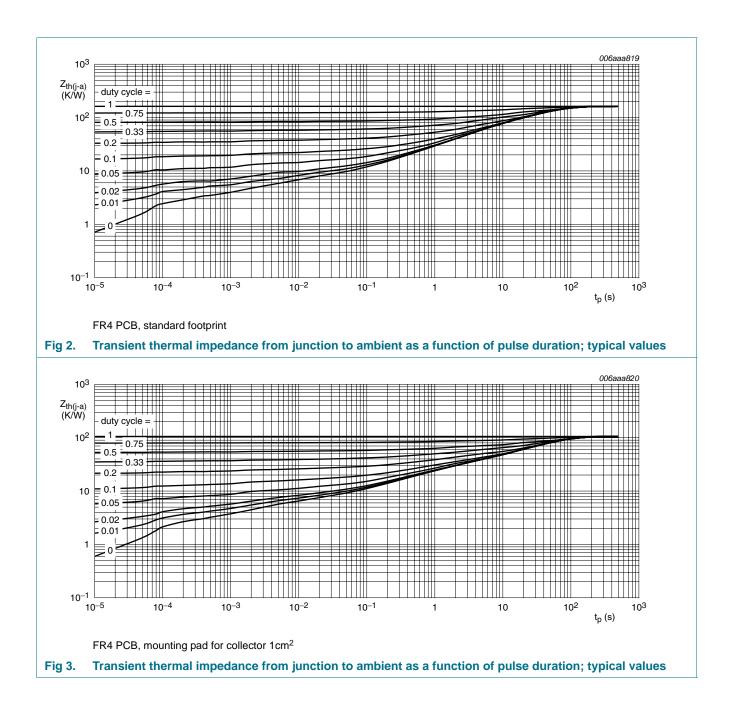
Symbol	Parameter	Conditions	Min	Тур	Max	Unit
R _{th(j-a)}	thermal resistance from	in free air	<u>[1]</u> _	-	192	K/W
	junction to ambient		[2] _	-	125	K/W
			[3]	-	89	K/W
R _{th(j-sp)}	thermal resistance from junction to solder point		-	-	17	K/W

[1] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.

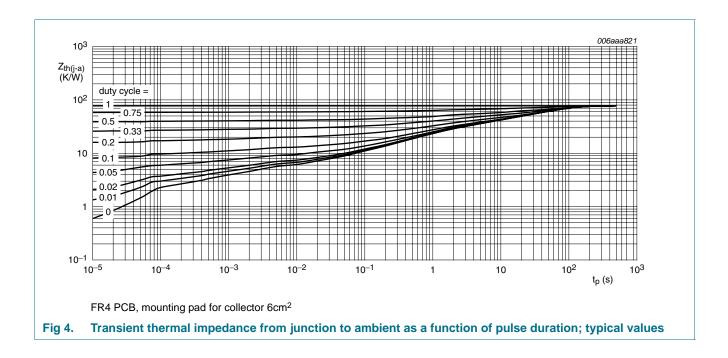
[2] Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for collector 1cm².

[3] Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for collector 6cm².

PBSS9110Z



PBSS9110Z



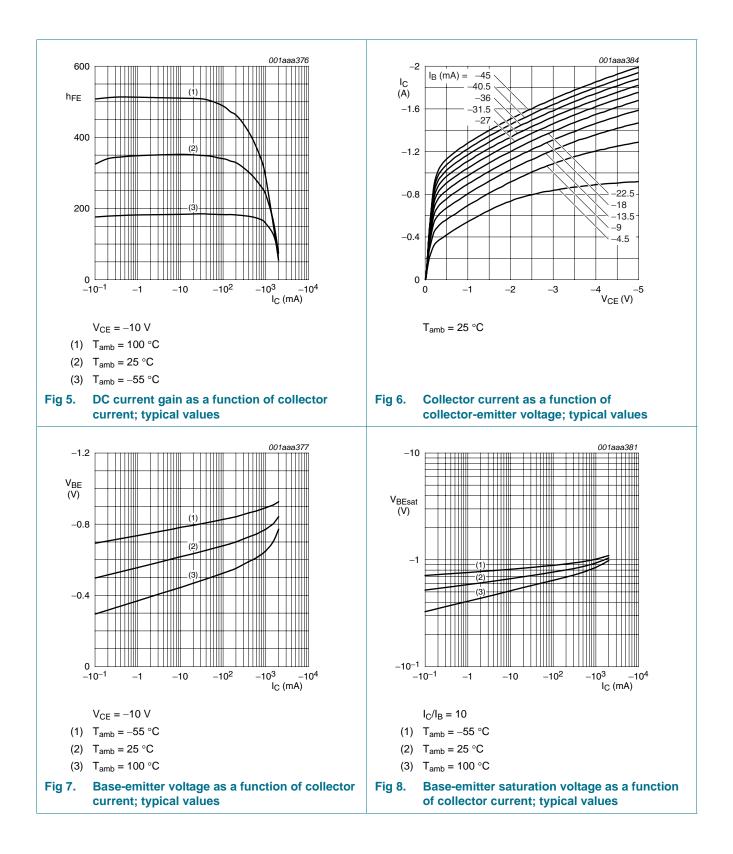
100 V, 1 A PNP low V_{CEsat} (BISS) transistor

7. Characteristics

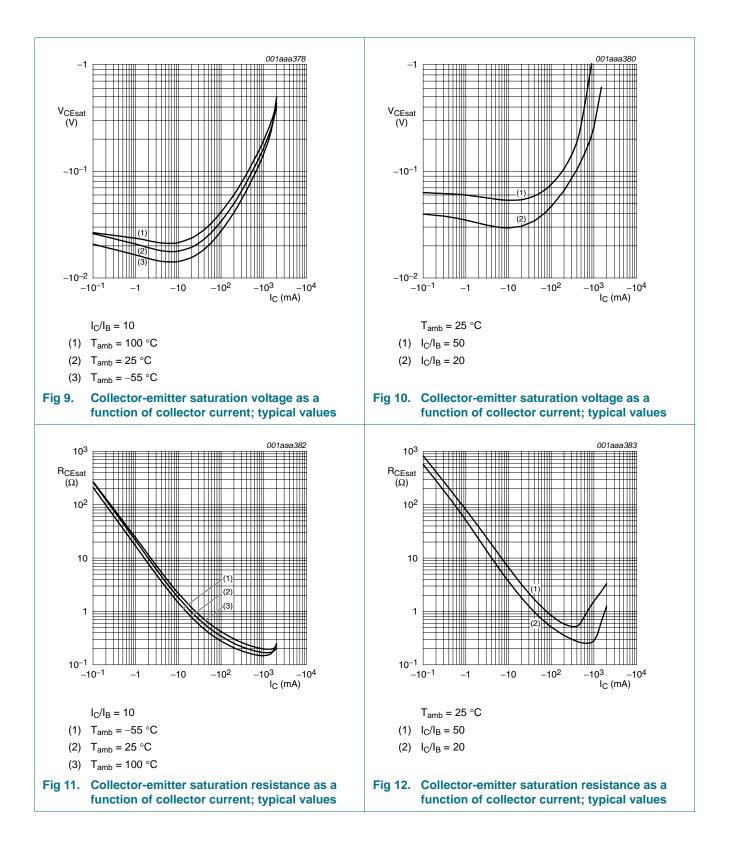
Symbol	Parameter	Conditions		Min	Тур	Max	Unit
I _{CBO}	collector-base cut-off	$V_{CB} = -80 \text{ V}; \text{ I}_{E} = 0 \text{ A}$		-	-	-100	nA
	current	V _{CB} = -80 V; I _E = 0 A; T _j = 150 °C		-	-	-50	μΑ
I _{CES}	collector-emitter cut-off current	V _{CE} = -80 V; V _{BE} = 0 V		-	-	-100	nA
I _{EBO}	emitter-base cut-off current	$V_{EB} = -4 \text{ V; } I_C = 0 \text{ A}$		-	-	-100	nA
h _{FE}	DC current gain	$V_{CE} = -5 V;$ $I_C = -1 mA$		150	-	-	
		$V_{CE} = -5 V;$ $I_{C} = -250 \text{ mA}$		150	-	-	
		$V_{CE} = -5 V;$ $I_{C} = -0.5 A$	<u>[1]</u>	150	-	450	
		V_{CE} = -5 V; I_C = -1 A	[1]	125	-	-	
V _{CEsat}	collector-emitter saturation voltage	I _C = −250 mA; I _B = −25 mA		-	-	-120	mV
		I _C = -500 mA; I _B = -50 mA	<u>[1]</u>	-	-	-180	mV
		I _C = -1 A; I _B = -100 mA	<u>[1]</u>	-	-	-320	mV
R _{CEsat}	collector-emitter saturation resistance	I _C = -1 A; I _B = -100 mA	<u>[1]</u>	-	170	320	mΩ
V _{BEsat}	base-emitter saturation voltage	I _C = -1 A; I _B = -100 mA	<u>[1]</u>	-	-	-1.1	V
V _{BEon}	base-emitter turn-on voltage	V_{CE} = -5 V; I_C = -1 A	<u>[1]</u>	-	-	-1.0	V
t _d	delay time	$V_{CC} = -10 V;$		-	20	-	ns
t _r	rise time	I _C = -0.5 A; I _{Bon} = -0.025 A;		-	60	-	ns
on	turn-on time	$I_{Boff} = 0.025 \text{ A},$		-	80	-	ns
t _s	storage time			-	290	-	ns
t _f	fall time			-	120	-	ns
t _{off}	turn-off time			-	410	-	ns
fT	transition frequency	$V_{CE} = -10 V;$ $I_{C} = -50 mA;$ f = 100 MHz		100	-	-	MHz
C _c	collector capacitance	$V_{CB} = -10 V;$ $I_E = i_e = 0 A;$ f = 1 MHz		-	-	17	pF

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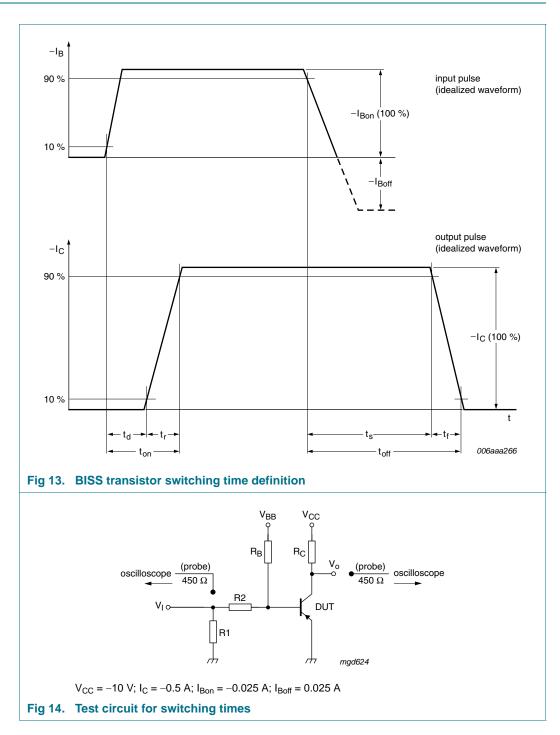


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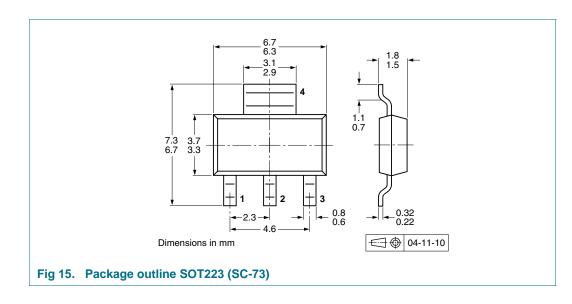
100 V, 1 A PNP low V_{CEsat} (BISS) transistor

8. Test information



100 V, 1 A PNP low V_{CEsat} (BISS) transistor

9. Package outline



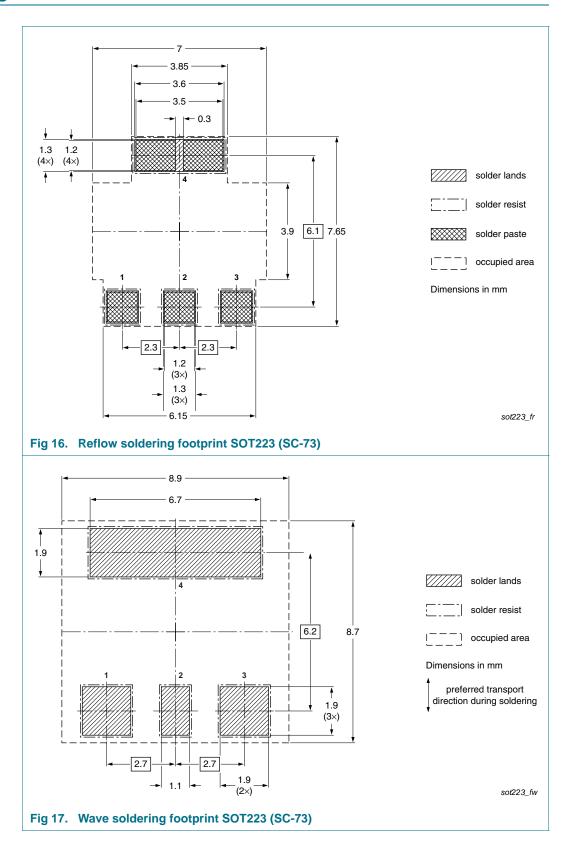
10. Packing information

	king metho xxx are the la	ds ast three digits of the 12NC ordering code	<u>[1]</u>	
Type number	Package	Description	Packing	quantity
			1000	4000
PBSS9110Z	SOT223	8 mm pitch, 12 mm tape and reel	-115	-135

[1] For further information and the availability of packing methods, see <u>Section 14</u>.

100 V, 1 A PNP low V_{CEsat} (BISS) transistor

11. Soldering



100 V, 1 A PNP low V_{CEsat} (BISS) transistor

12. Revision history

Table 9. Revision	history			
Document ID	Release date	Data sheet status	Change notice	Supersedes
PBSS9110Z_3	20091211	Product data sheet	-	PBSS9110Z_2
Modifications:		sheet was changed to reflec ew legal definitions and dise		
	Figure 16 '	Reflow soldering footprint S	OT223 (SC-73)": update	ed
	Figure 17 '	Wave soldering footprint SC	DT223 (SC-73)": updated	I
PBSS9110Z_2	20060724	Product data sheet	-	PBSS9110Z_1
PBSS9110Z_1	20040609	Product data sheet	-	-

100 V, 1 A PNP low V_{CEsat} (BISS) transistor

13. Legal information

13.1 Data sheet status

Document status ^{[1][2]}	Product status ^[3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

[1] Please consult the most recently issued document before initiating or completing a design.

[2] The term 'short data sheet' is explained in section "Definitions".

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PBSS9110Z_3

PBSS9110Z

100 V, 1 A PNP low V_{CEsat} (BISS) transistor

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